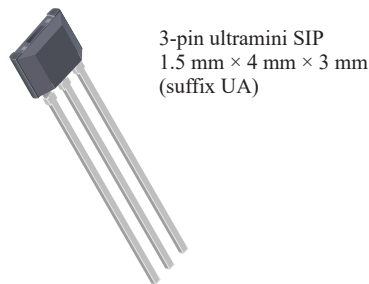# ALLEGRO microsystems

ALS31001LUAA

Linear Hall-Effect Sensor IC with Analog Output, in Ultramini Through-Hole Package

FEATURES AND BENEFITS

• 3.3 or 5.0 V supply operation
• QVO temperature coefficient programmed at Allegro™ for improved accuracy
• High-bandwidth, low-noise analog output
• High-speed chopping scheme minimizes QVO drift across operating temperature range
• Temperature-stable quiescent voltage output and sensitivity
• Precise recoverability after temperature cycling
• Output voltage clamps provide short-circuit diagnostic capabilities
• Undervoltage lockout (UVLO)
• Wide ambient temperature range: –40°C to 150°C
• Immune to mechanical stress
• Enhanced EMC performance for stringent automotive applications
• Small package size

PACKAGE:

3-pin ultramini SIP
1.5 mm × 4 mm × 3 mm
(suffix UA)

Not to scale

DESCRIPTION

New applications for linear output Hall-effect sensors, such as displacement and angular position, require higher accuracy and smaller package sizes. The Allegro ALS31001LUAA linear Hall-effect sensor IC has been designed specifically to meet both requirements.

The accuracy of this device is enhanced via end-of-line optimization. The ALS31001LUAA features non-volatile memory to optimize device sensitivity and the quiescent voltage output (QVO: output in the absence of a magnetic field) for a given application or circuit. Optimized performance is sustained across the full operating temperature range by programming the temperature coefficient for both sensitivity and QVO at Allegro end-of-line test.
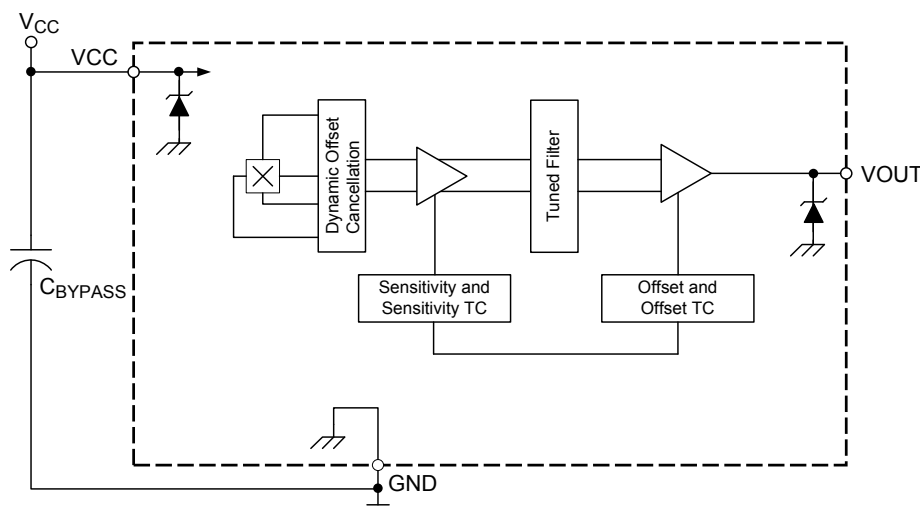
This ratiometric Hall-effect sensor IC provides a voltage output proportional to the applied magnetic field. The quiescent voltage output is adjusted around 50% of the supply voltage.

The features of this linear device make it ideal for use in automotive and industrial applications requiring high accuracy and operation across an extended temperature range, –40°C to 150°C.

Each BiCMOS monolithic circuit integrates: a Hall element, temperature-compensating circuitry to reduce the intrinsic sensitivity drift of the Hall element, a small-signal high-gain amplifier, a clamped low-impedance output stage, and a proprietary dynamic offset cancellation technique.

Continued on the next page…

Functional Block Diagram

DESCRIPTION (CONTINUED)

The ALS31001LUAA sensor IC is offered in the UA package style: a 3-pin ultramini single inline package (SIP) for through-hole mounting. The package is lead (Pb) free, with 100% matte-tin leadframe plating.

SELECTION GUIDE

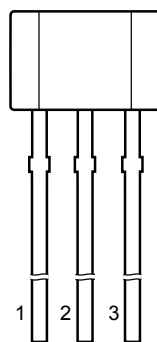| Part Number	Output Polarity	Nominal Supply Voltage (V)	Sensitivity (typ) (mV/G)	Packing*	Package
ALS31001LUAATN	Forward	3.3	1.8	4000 pieces per 13-inch reel	3-pin SIP through-hole
ALS31001LUAATN-5V	Forward	5.0	2.5		

*Contact Allegro™ for additional packing options

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Notes	Rating	Unit
Forward Supply Voltage	V_{CC}		8	V
Reverse Supply Voltage	V_{RCC}		–0.1	V
Forward Output Voltage	V_{OUT}		7	V
Reverse Output Voltage	V_{ROUT}		–0.1	V
Output Source Current	$I_{OUT(SOURCE)}$	VOUT to GND	2	mA
Output Sink Current	$I_{OUT(SINK)}$	VCC to VOUT	10	mA
Operating Ambient Temperature	T_A	Range L	–40 to 150	°C
Maximum Junction Temperature	$T_J(max)$		165	°C
Storage Temperature	T_{stg}		–65 to 170	°C

THERMAL CHARACTERISTICS: May require derating at maximum conditions; see application information

Characteristic	Symbol	Test Conditions	Value	Units
Package Thermal Resistance	$R_{\theta JA}$	Package UA, 1-layer PCB with copper limited to solder pads	165	°C/W

Pinout Diagram

UA Package

Terminal List Table

Name	Number	Description
VCC	1	Input power supply; tie to GND with bypass capacitor
GND	2	Ground
VOUT	3	Output signal

OPERATING CHARACTERISTICS: Valid over T_A , C_{BYPASS} = 0.1 µF, and nominal V_{CC}, unless otherwise noted

Characteristic	Symbol	Test Conditions	Min.	Typ.	Max.	Unit [1]
ELECTRICAL CHARACTERISTICS						
Supply Voltage	V_{CC}	ALS31001LUAA-TN	3.0	3.3	3.6	V
		ALS31001LUAATN-5V	4.5	5.0	5.5	V
Undervoltage Threshold [2]	V_{UVLOHI}	Tested at T_A = 25°C and T_A = 150°C (device powers-on)	–	–	3	V
	V_{UVLOLO}	Tested at T_A = 25°C and T_A = 150°C (device powers-off)	2.5	–	–	V
Supply Current	I_{CC}	ALS31001LUAATN	–	4.2	5.5	mA
		ALS31001LUAATN-5V	–	–	8	mA
Power-On Time [3][4]	t_{PO}	T_A = 25°C, $C_{L(PROBE)}$ = 10 pF	–	50	–	µs
V_{CC} Ramp Time [3][4]	t_{VCC}	T_A = 25°C	0.005	–	100	ms
V_{CC} Off Level [3][4]	V_{CCOFF}	T_A = 25°C	0	–	0.33	V
Delay to Clamp [3][4]	t_{CLP}	T_A = 25°C, C_L = 0.22 nF	–	30	–	µs
Supply Zener Clamp Voltage	V_Z	T_A = 25°C, I_{CC} = 13 mA	6	7.3	–	V
Internal Bandwidth [4]	BW_i	Small signal –3 dB	–	20	–	kHz
Chopping Frequency [5]	f_C	T_A = 25°C	–	400	–	kHz
OUTPUT CHARACTERISTICS						
Output Referred Noise [4]	V_N	V_{CC} = 3.3 V, T_A = 25°C, C_L = open, Sens = 1.8 mV/G, no load on VOUT	–	4.9	–	$mV_{(p-p)}$
Input Referred RMS Noise Density [4]	V_{NRMS}	V_{CC} = 3.3 V, T_A = 25°C, C_L = open, Sens = 1.8 mV/G, no load on VOUT, $f_{measured} \ll 1 \dots 10$ kHz	–	3.0	–	mG/√Hz
DC Output Resistance [4]	R_{OUT}		–	3	–	Ω
Output Load Resistance [4]	R_L	VOUT to GND	10	–	–	kΩ
Output Load Capacitance [4]	C_L	VOUT to GND	–	–	0.22	nF
Output Voltage Clamps [6][11]	$V_{CLPHIGH}$	ALS31001LUAATN; T_A = 25°C, B = +1000 G, R_L = 10 kΩ (VOUT to GND)	2.842	2.97	3.069	V
		ALS31001LUAATN-5V; T_A = 25°C, B = +1000 G, R_L = 10 kΩ (VOUT to GND)	4.30	4.5	4.70	V
	V_{CLPLOW}	ALS31001LUAATN; T_A = 25°C, B = –1000 G, R_L = 10 kΩ (VOUT to GND)	0.264	0.33	0.462	V
		ALS31001LUAATN-5V; T_A = 25°C, B = –1000 G, R_L = 10 kΩ (VOUT to GND)	0.35	0.55	0.75	V
Sensitivity [7]	Sens	T_A = 25°C, ALS31001LUAATN	1.71	1.80	1.89	mV/G
		T_A = 25°C, ALS31001LUAATN-5V	2.42	2.5	2.58	mV/G
Quiescent Voltage Output (QVO)	$V_{OUT(Q)}$	T_A = 25°C, ALS31001LUAATN	1.61	1.65	1.69	V
		T_A = 25°C, ALS31001LUAATN-5V	2.368	2.4	2.432	V
Sensitivity Temperature Coefficient	TC_{Sens}	Programmed at T_A = 150°C, calculated relative to Sens at 25°C; ALS31001LUAATN	0.08	0.12	0.16	%/°C
		Programmed at T_A = 150°C, calculated relative to Sens at 25°C; ALS31001LUAATN-5V	0.10	0.13	0.16	%/°C

Continued on the next page…

OPERATING CHARACTERISTICS (continued): Valid over T_A , C_{BYPASS} = 0.1 µF, and nominal V_{CC}, unless otherwise noted

Characteristic	Symbol	Test Conditions	Min.	Typ.	Max.	Unit[1]
ERROR COMPONENTS						
Linearity Sensitivity Error	Lin_{ERR}		–	±1.5	–	%
Symmetry Sensitivity Error	Sym_{ERR}		–	±1.5	–	%
Ratiometry Quiescent Voltage Output Error [8]	$Rat_{VOUT(Q)}$	Across supply voltage range (relative to nominal V_{CC})	–	±1.5	–	%
Ratiometry Sensitivity Error [8][9]	Rat_{Sens}	Across supply voltage range (relative to nominal V_{CC})	–	±1.5	–	%
Ratiometry Clamp Error [10]	$Rat_{VOUTCLP}$	T_A = 25°C, across supply voltage range (relative to nominal V_{CC})	–	±1.5	–	%
DRIFT CHARACTERISTICS						
Typical Quiescent Voltage Output Drift Across Temperature Range	$\Delta V_{OUT(Q)}$	T_A = 150°C	−23	0	23	mV
Sensitivity Drift Due to Package Hysteresis	$\Delta Sens_{PKG}$	T_A = 25°C, after temperature cycling	–	±2	–	%

[1] 1 G (gauss) = 0.1 mT (millitesla),
[2] On power-up, the output of the device is held low until V_{CC} exceeds V_{UVLOHI}. After the device is powered, the output remains valid until V_{CC} drops below V_{UVLOLO}, when the output is pulled low.
[3] See the Characteristic Definitions section.
[4] Determined by design and characterization, not evaluated at final test.
[5] f_C varies as much as approximately ±20% across the full operating ambient temperature range and process.
[6] V_{CLPLOW} and $V_{CLPHIGH}$ scale with V_{CC} due to ratiometry.
[7] Sensitivity drift through the life of the part, $\Delta Sens_{LIFE}$, can have a typical error value ±3% in addition to package hysteresis effects.
[8] Percent change from actual value at nominal V_{CC}, for a given temperature.
[9] Cold temperature may exhibit up to 8% Ratiometry Sensitivity Error.
[10] Percent change from actual value at nominal V_{CC}, T_A = 25°C.
[11] Tested at wafer probe.

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CHARACTERISTIC DEFINITIONS

Power-On Time. When the supply is ramped to its operating voltage, the device output requires a finite time to react to an input magnetic field. Power-On Time, t_{PO}, is defined as the time it takes for the output voltage to begin responding to an applied magnetic field after the power supply has reached its minimum specified operating voltage, V_{CC} (min), as shown in figure 1.

Delay to Clamp. A large magnetic input step may cause the clamp to overshoot its steady-state value. The Delay to Clamp, t_{CLP}, is defined as the time it takes for the output voltage to settle within 1% of its steady-state value, after initially passing through its steady-state voltage, as shown in figure 2.
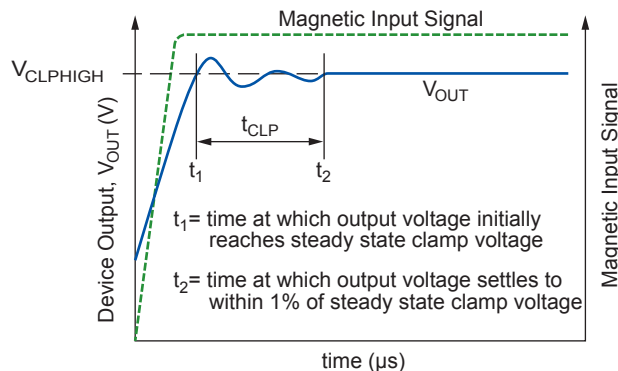

Figure 1. Definition of Power On Time, t_{PO}

Figure 2. Definition of Delay to Clamp, t_{CLP}

Quiescent Voltage Output. In the quiescent state (no significant magnetic field: B = 0 G), the output, $V_{OUT(Q)}$, is at a constant ratio to the supply voltage, V_{CC}, across the entire operating ranges of V_{CC} and Operating Ambient Temperature, T_A.

Quiescent Voltage Output Drift Across Temperature Range. Due to internal component tolerances and thermal considerations, the Quiescent Voltage Output, $V_{OUT(Q)}$, may drift due to temperature changes within the Operating Ambient Temperature, T_A. For purposes of specification, the Quiescent Voltage Output Drift Across Temperature Range, $\Delta V_{OUT(Q)}$ (mV), is defined as:

$$\Delta V_{OUT(Q)} = V_{OUT(Q)(TA)} - V_{OUT(Q)(25°C)} \tag{1}$$

Sensitivity. The amount of the output voltage change is proportional to the magnitude and polarity of the magnetic field applied. This proportionality is specified as the magnetic sensitivity, Sens (mV/G), of the device and is defined as:

$$\text{Sens} = \frac{V_{OUT(B+)} - V_{OUT(B-)}}{(B+) - (B-)} \tag{2}$$

where B+ is the magnetic flux density in a positive field (south polarity) and B– is the magnetic flux density in a negative field (north polarity).

Sensitivity Temperature Coefficient. The device sensitivity changes as temperature changes, with respect to its Sensitivity Temperature Coefficient, TC_{SENS}. TC_{SENS} is programmed at 150°C, and calculated relative to the baseline sensitivity programming temperature of 25°C. TC_{SENS} is defined as:

$$TC_{Sens} = \left(\frac{\text{Sens}_{T2} - \text{Sens}_{T1}}{\text{Sens}_{T1}} \times 100\right)\left(\frac{1}{T2 - T1}\right) \quad (\%/°C) \tag{3}$$

where T1 is the baseline Sens programming temperature of 25°C, and T2 is the TC_{SENS} programming temperature of 150°C.

The ideal value of Sens across the full ambient temperature range, $\text{Sens}_{IDEAL(TA)}$, is defined as:

$$\text{Sens}_{IDEAL(TA)} = \text{Sens}_{T1} \times [100\,(\%) + TC_{SENS}\,(T_A - T1)] \tag{4}$$

Sensitivity Drift Across Temperature Range. Second order sensitivity temperature coefficient effects cause the magnetic sensitivity, Sens, to drift from its ideal value across the operating ambient temperature range, T_A. For purposes of specification,

5

the Sensitivity Drift Across Temperature Range, $\Delta Sens_{TC}$, is defined as:

$$\Delta Sens_{TC} = \frac{Sens_{TA} - Sens_{IDEAL(TA)}}{Sens_{IDEAL(TA)}} \times 100 \quad (\%) \quad (5)$$

Sensitivity Drift Due to Package Hysteresis. Package stress and relaxation can cause the device sensitivity at $T_A = 25°C$ to change during and after temperature cycling. This change in sensitivity follows a hysteresis curve. For purposes of specification, the Sensitivity Drift Due to Package Hysteresis, $\Delta Sens_{PKG}$, is defined as:

$$\Delta Sens_{PKG} = \frac{Sens_{(25°C)(2)} - Sens_{(25°C)(1)}}{Sens_{(25°C)(1)}} \times 100 \quad (\%) \quad (6)$$

where $Sens_{(25°C)(1)}$ is the programmed value of sensitivity at $T_A = 25°C$, and $Sens_{(25°C)(2)}$ is the value of sensitivity at $T_A = 25°C$ after temperature cycling T_A up to 150°C, down to –40°C, and back to up 25°C.

Linearity Sensitivity Error. The ALS31001LUAA is designed to provide linear output in response to a ramping applied magnetic field. Consider two magnetic fields, B1 and B2. Ideally, the sensitivity of a device is the same for both fields, for a given supply voltage and temperature. Linearity error is present when there is a difference between the sensitivities measured at B1 and B2.

Linearity Sensitivity Error, LIN_{ERR}, is calculated separately for positive (Lin_{ERR+}) and negative (Lin_{ERR-}) applied magnetic fields. LIN_{ERR} (%) is measured and defined as:

$$Lin_{ERR+} = \left(1 - \frac{Sens_{(B+)(2)}}{Sens_{(B+)(1)}}\right) \times 100 \quad (\%) \quad (7)$$

$$Lin_{ERR-} = \left(1 - \frac{Sens_{(B-)(2)}}{Sens_{(B-)(1)}}\right) \times 100 \quad (\%)$$

where:

$$Sens_{Bx} = \frac{|V_{OUT(Bx)} - V_{OUT(Q)}|}{B_x} \quad (8)$$

and Bx are positive and negative magnetic fields, with respect to the quiescent voltage output, such that

$$|B_{(+)(2)}| > |B_{(+)(1)}| \text{ and } |B_{(-)(2)}| > |B_{(-)(1)}|$$

The effective linearity error is:

$$Lin_{ERR} = \max(|Lin_{ERR+}| , |Lin_{ERR-}|) \quad (9)$$

The output voltage clamps, $V_{CLPHIGH}$ and V_{CLPLOW}, limit the operating magnetic range of the applied field in which the device provides a linear output. The maximum positive and negative applied magnetic fields in the operating range can be calculated:

$$|B_{MAX(+)}| = \frac{V_{CLPHIGH} - V_{OUT(Q)}}{Sens} \quad (10)$$

$$|B_{MAX(-)}| = \frac{V_{OUT(Q)} - V_{CLPLOW}}{Sens}$$

Symmetry Sensitivity Error. The magnetic sensitivity of the device is constant for any two applied magnetic fields of equal magnitude and opposite polarities. Symmetry error, Sym_{ERR} (%), is measured and defined as:

$$Sym_{ERR} = \left(1 - \frac{Sens_{(B+)}}{Sens_{(B-)}}\right) \times 100 \quad (\%) \quad (11)$$

where $Sens_{Bx}$ is as defined in equation 10, and B+ and B– are positive and negative magnetic fields such that $|B+| = |B-|$.

Ratiometry Error. The ALS31001LUAA provides ratiometric output. This means that the Quiescent Voltage Output, $V_{OUT(Q)}$, magnetic sensitivity, Sens, and clamp voltages, $V_{CLPHIGH}$ and V_{CLPLOW}, are proportional to the supply voltage, V_{CC}. In other words, when the supply voltage increases or decreases by a certain percentage, each characteristic also increases or decreases by the same percentage. Error is the difference between the measured change in the supply voltage relative to the nominal V_{CC} level (3.3 V or 5.0 V), and the measured change in each characteristic. Equations below show examples for a 3.3 V supply device.

The ratiometric error in quiescent voltage output, $Rat_{VOUT(Q)}$ (%), for a given supply voltage, V_{CC}, is defined as:

$$Rat_{VOUT(Q)} = \left(1 - \frac{V_{OUT(Q)(VCC)} / V_{OUT(Q)(3.3V)}}{V_{CC} / 3.3 \ (V)}\right) \times 100 \quad (\%) \quad (12)$$

The ratiometric error in magnetic sensitivity, Rat_{Sens} (%), for a given supply voltage, V_{CC}, is defined as:

$$Rat_{Sens} = \left(1 - \frac{Sens_{(VCC)} / Sens_{(3.3V)}}{V_{CC} / 3.3 \ (V)}\right) \times 100 \quad (\%) \quad (13)$$

The ratiometric error in the clamp voltages, $Rat_{VOUTCLP}$ (%), for a given supply voltage, V_{CC}, is defined as:

$$Rat_{VOUTCLP} = \left(1 - \frac{V_{CLP(VCC)} / V_{CLP(3.3V)}}{V_{CC} / 3.3 \ (V)}\right) \times 100 \quad (\%) \quad (14)$$

where V_{CLP} is either $V_{CLPHIGH}$ or V_{CLPLOW}.

Undervoltage Lockout. The ALS31001LUAA provides an undervoltage lockout feature which ensures that the device outputs a VOUT signal only when V_{CC} is above certain thresholds. The undervoltage lockout feature provides a hysteresis of operation to eliminate indeterminate output states.

The output of the ALS31001LUAA is held low (GND) until V_{CC} exceeds V_{UVLOHI}. After V_{CC} exceeds V_{UVLOHI}, the device VOUT output is enabled, providing a ratiometric output voltage that is proportional to the input magnetic signal and V_{CC}. If V_{CC} should drop back down below V_{UVLOLO} for longer than t_{UVLO} after the device is powered up, the output would be pulled low (see figure 3) until V_{UVLOHI} is reached again and VOUT would be reenabled.

V_{CC} Ramp Time. The time taken for V_{CC} to ramp from 0 V to $V_{CC}(typ)$ (see figure 4).

V_{CC} Off Level. For applications in which the VCC pin of the ALS31001LUAA is being power-cycled (for example using a multiplexer to toggle the part on and off), the specification of V_{CC} Off Level, V_{CCOFF}, determines how high a V_{CC} off voltage can be tolerated while still ensuring proper operation and startup of the device (see figure 4).
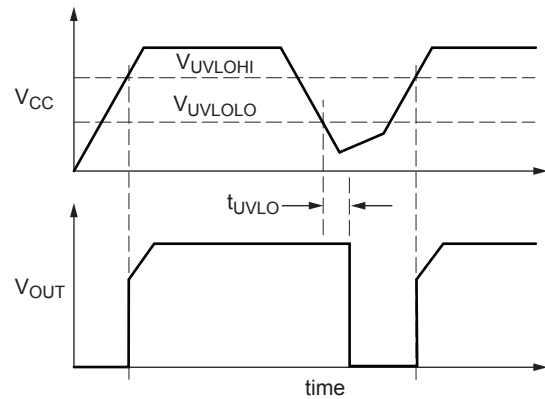

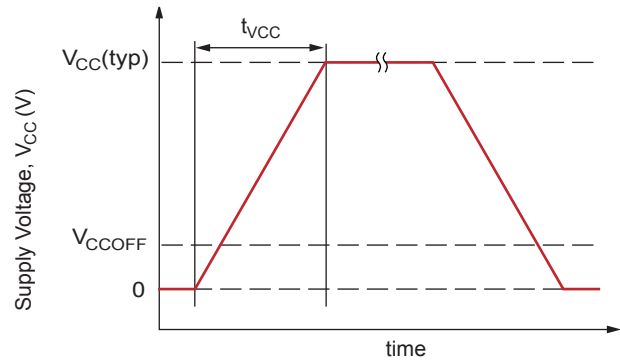Figure 3. Definition of Undervoltage Lockout

Figure 4. Definition of V_{CC} Ramp Time, t_{VCC}
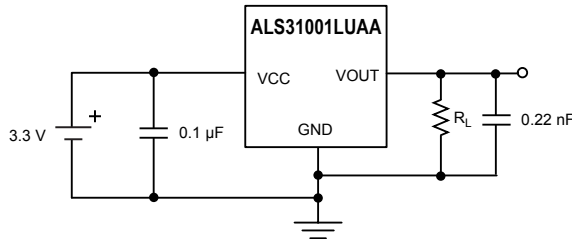
APPLICATION INFORMATION

Figure 5. Typical Application Circuit

CHOPPER STABILIZATION TECHNIQUE

When using Hall-effect technology, a limiting factor for switchpoint accuracy is the small-signal voltage developed across the Hall element. This voltage is disproportionally small relative to the offset that can be produced at the output of the Hall sensor IC. This makes it difficult to process the signal while maintaining an accurate, reliable output over the specified operating temperature and voltage ranges. Chopper stabilization is a unique approach used to minimize Hall offset on the chip. Allegro employs a technique to remove key sources of the output drift induced by thermal and mechanical stresses. This offset reduction technique is based on a signal modulation-demodulation process. The undesired offset signal is separated from the magnetic field-induced signal in the frequency domain, through modulation. The subsequent demodulation acts as a modulation process for the offset, causing the magnetic field-induced signal to recover its original spectrum at base band, while the DC offset becomes a high-frequency signal. The magnetic-sourced signal then can pass through a low-pass filter, while the modulated DC offset is suppressed. In addition to the removal of the thermal and mechanical stress related offset, this novel technique also reduces the amount of thermal noise in the Hall sensor IC while completely removing the modulated residue resulting from the chopper operation. The chopper stabilization technique uses a high-frequency sampling clock. For demodulation process, a sample-and-hold technique is used. This high-frequency operation allows a greater sampling rate, which results in higher accuracy and faster signal-processing capability. This approach desensitizes the chip to the effects of thermal and mechanical stresses, and produces devices that have extremely stable quiescent Hall output voltages and precise recoverability after temperature cycling. This technique is made possible through the use of a BiCMOS process, which allows the use of low-offset, low-noise amplifiers in combination with high-density logic integration and sample-and-hold circuits.
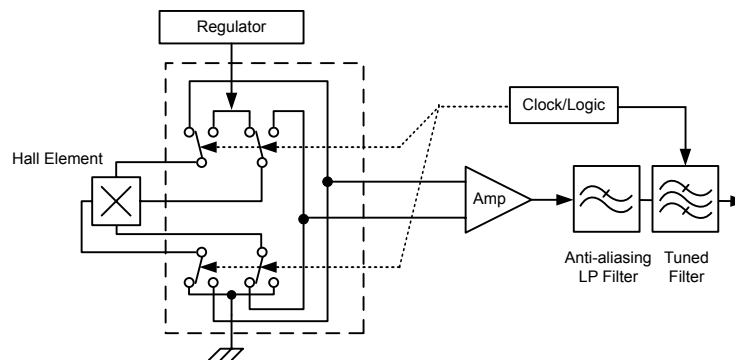

Figure 6. Chopper Stabilization Technique
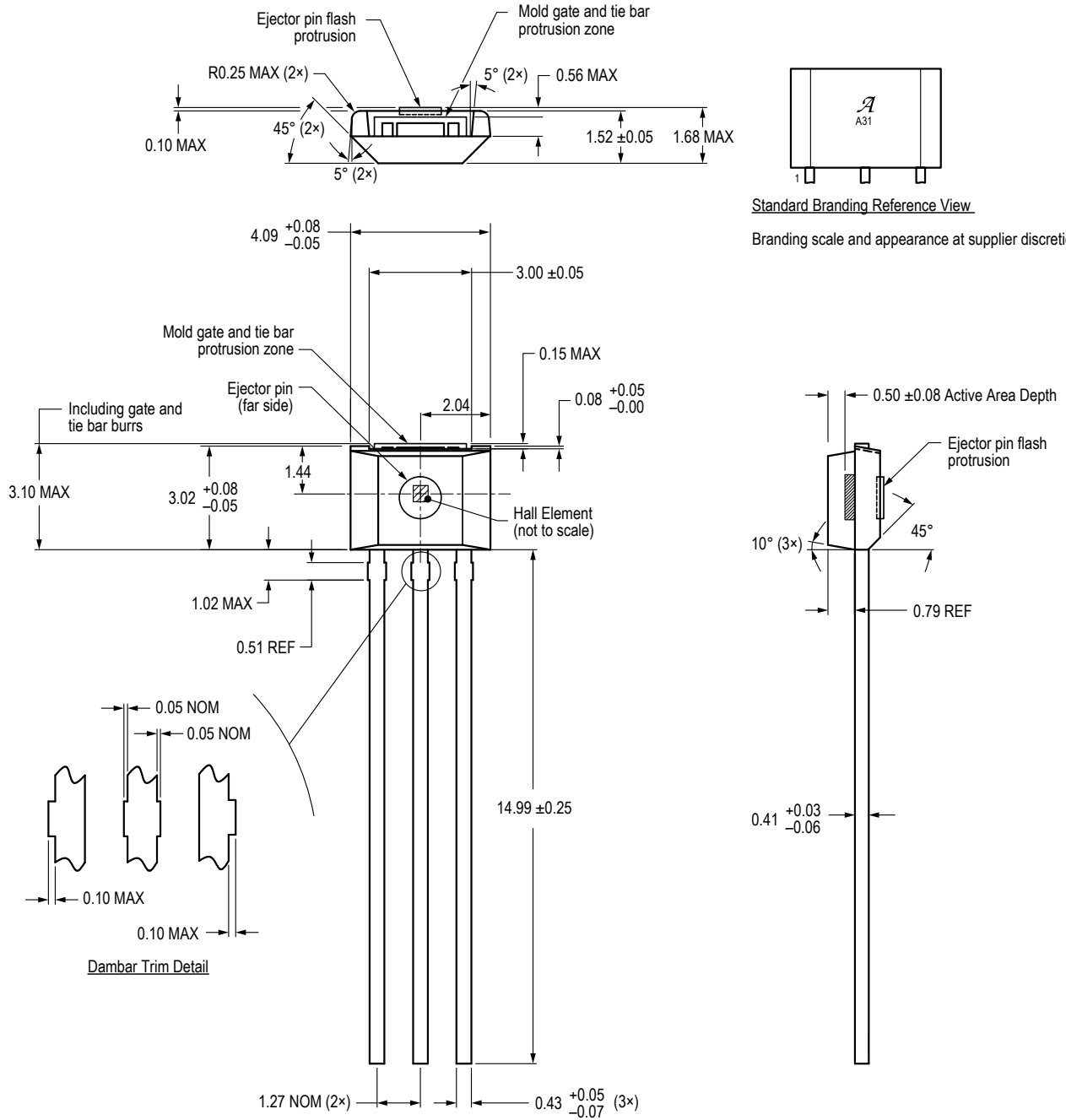
Package UA, 3-Pin SIP

For Reference Only – Not For Tooling Use

(Reference DWG-0000404, Rev. 1)
NOT TO SCALE
Dimensions in millimeters
Exact case and lead configuration at supplier discretion within limits shown

Ejector pin flash protrusion

Mold gate and tie bar protrusion zone

R0.25 MAX (2×)

5° (2×)

0.56 MAX

45° (2×)

0.10 MAX

1.52 ±0.05

1.68 MAX

5° (2×)

Standard Branding Reference View

Branding scale and appearance at supplier discretion

$\mathcal{A}$
A31

1

4.09 +0.08 −0.05

3.00 ±0.05

Mold gate and tie bar protrusion zone

0.15 MAX

Ejector pin (far side)

2.04

0.08 +0.05 −0.00

Including gate and tie bar burrs

1.44

3.10 MAX

3.02 +0.08 −0.05

Hall Element (not to scale)

0.50 ±0.08 Active Area Depth

Ejector pin flash protrusion

10° (3×)

45°

1.02 MAX

0.51 REF

0.79 REF

0.05 NOM

0.05 NOM

14.99 ±0.25

0.41 +0.03 −0.06

0.10 MAX

0.10 MAX

Dambar Trim Detail

1.27 NOM (2×)

0.43 +0.05 −0.07 (3×)

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Revision History

Number	Date	Description
–	November 28, 2017	Initial release
1	January 11, 2019	Minor editorial updates
2	January 20, 2020	Minor editorial updates
3	March 24, 2020	Added 5 V supply voltage variant
4	March 31, 2020	Updated Output Voltage Clamps characteristic (page 3)
5	April 20, 2020	Updated Output Voltage Clamps characteristic (page 3)
6	April 23, 2020	Updated part numbers (pages 2-3)
7	May 4, 2021	Updated Package Outline Drawing reference number and active area depth (page 9)
8	May 13, 2022	Updated Package Outline Drawing (page 9)

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Allegro MicroSystems
955 Perimeter Road
Manchester, NH 03103-3353 U.S.A.
www.allegromicro.com